

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The ASI TVU001 is Designed for

**FEATURES:**

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- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	1.2 A
<b>V<sub>CB0</sub></b>	45 V
<b>V<sub>CEO</sub></b>	25 V
<b>V<sub>EBO</sub></b>	3.5 V
<b>P<sub>DISS</sub></b>	19.4 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	12 °C/W

**PACKAGE STYLE .280 4L STUD**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

**ORDER CODE: ASI10643**

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CB0</sub></b>	I <sub>C</sub> = 2.0 mA	45			<b>V</b>
<b>BV<sub>CER</sub></b>	I <sub>C</sub> = 40 mA      R <sub>BE</sub> = 10 Ω	50			<b>V</b>
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 40 mA	24			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 0.5 mA	3.5			<b>V</b>
<b>I<sub>CB0</sub></b>	V <sub>CB</sub> = 28 V			0.45	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 200 mA	200		120	<b>---</b>
<b>C<sub>OB</sub></b>	V <sub>CB</sub> = 20 V      f = 1.0 MHz			7	<b>pF</b>
<b>P<sub>G</sub> IMD<sub>1</sub></b>	V <sub>CE</sub> = 20 V      I <sub>C</sub> = 440 mA      f = 860 MHz P <sub>OUT</sub> = 1.0 W	10 -60			<b>dB dBc</b>